

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV11** is Designed for Class C, 12.5 Volt operation in FM Amplifier Applications up to 250 MHz.

FEATURES INCLUDE:

- $P_G = 9.0$ dB Typical at 175 MHz
- Emitter Ballasting
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CE}	18 V
V_{CB}	36 V
P_{DISS}	37 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.6 °C/W

PACKAGE STYLE .375 4L FLG																																			
<table border="1"> <thead> <tr> <th></th> <th>MINIMUM Inches/mm</th> <th>MAXIMUM Inches/mm</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>.220/.5,59</td> <td>.230/.5,84</td> </tr> <tr> <td>B</td> <td>.785/19,94</td> <td></td> </tr> <tr> <td>C</td> <td>.726/18,29</td> <td>.730/18,54</td> </tr> <tr> <td>D</td> <td>.970/24,64</td> <td>.980/24,89</td> </tr> <tr> <td>E</td> <td></td> <td>.385/9,78</td> </tr> <tr> <td>F</td> <td>.004/0,10</td> <td>.006/0,15</td> </tr> <tr> <td>G</td> <td>.085/2,16</td> <td>.105/2,67</td> </tr> <tr> <td>H</td> <td>.160/4,06</td> <td>.180/4,57</td> </tr> <tr> <td>I</td> <td></td> <td>.280/7,11</td> </tr> <tr> <td>J</td> <td>.240/6,10</td> <td>.255/6,48</td> </tr> </tbody> </table>			MINIMUM Inches/mm	MAXIMUM Inches/mm	A	.220/.5,59	.230/.5,84	B	.785/19,94		C	.726/18,29	.730/18,54	D	.970/24,64	.980/24,89	E		.385/9,78	F	.004/0,10	.006/0,15	G	.085/2,16	.105/2,67	H	.160/4,06	.180/4,57	I		.280/7,11	J	.240/6,10	.255/6,48	
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1 = Collector 2 = Base 3 & 4 = Emitter																																			
ORDER CODE: ASI10492																																			

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	36			V
BV_{CES}	$I_C = 50$ mA	36			V
BV_{CEO}	$I_C = 50$ mA	18			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	5.0	50		---
C_{ob}	$V_{CB} = 12.5$ V	$f = 1.0$ MHz	45		pF
P_G η_c	$V_{CE} = 13.5$ V	$P_{OUT} = 15$ W	$f = 175$ MHz	8.0 60	9.0 65
					dB %

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